Sep. 2022 / Vol. 179 Mitsubishi Electric

ADVANCE

Power Devices

CONTENTS

	Overview
Technical Reports	
	SiC Power Module for Automotive
	TH-Series: 7th Generation IGBT Modules for High-frequency Switching in Industrial Operation
	The Investigation of Humidity Absorption Behavior of Silicone Gel in HVIGBT Modules11 by <i>Kenji Hatori</i> and <i>Wakana Noboru</i>
	Built-in BSD-Function 600V High Voltage Integrated Circuit "M81777FP"
	Development of SiC Trench MOSFET with Novel Structure Enabling Lower Losses

Precis

Mitsubishi Electric's power modules, which employ the latest chip and package technology, realize ideal power electronics systems thanks to their high quality, low loss, and excellent noise performance.

• Editorial-Chief Hideyuki Ichiyama

Editorial Advisors

Masayuki Sato Hisao Takahashi Takumi Yurusa Yukiko Funada Hiroyuki Teranishi Kenichi Uto Tsutomu Matsubara Yasumasa Yamanaga Takao Ikai Takanori Ueda Hiroshi Usui Satoru Yamaguchi Hideya Tadokoro Yoshihiro Yamaguchi Kazuki Yamanaka Yuichiro Arata Toshihiro Kurita

Vol. 179 Feature Articles Editor Toru Matsuoka

Editorial Inquiries

Hideyuki Ichiyama Corporate Productivity Engineering & Logistics Dept. Fax: +81-3-3218-2465

Mitsubishi Electric Advance is published on line quarterly (in March, June, September, and December) by Mitsubishi Electric Corporation. Copyright © 2022 by Mitsubishi Electric Corporation; all rights reserved. Printed in Japan.

The company names and product names described herein are the trademarks or registered trademarks of the respective companies.